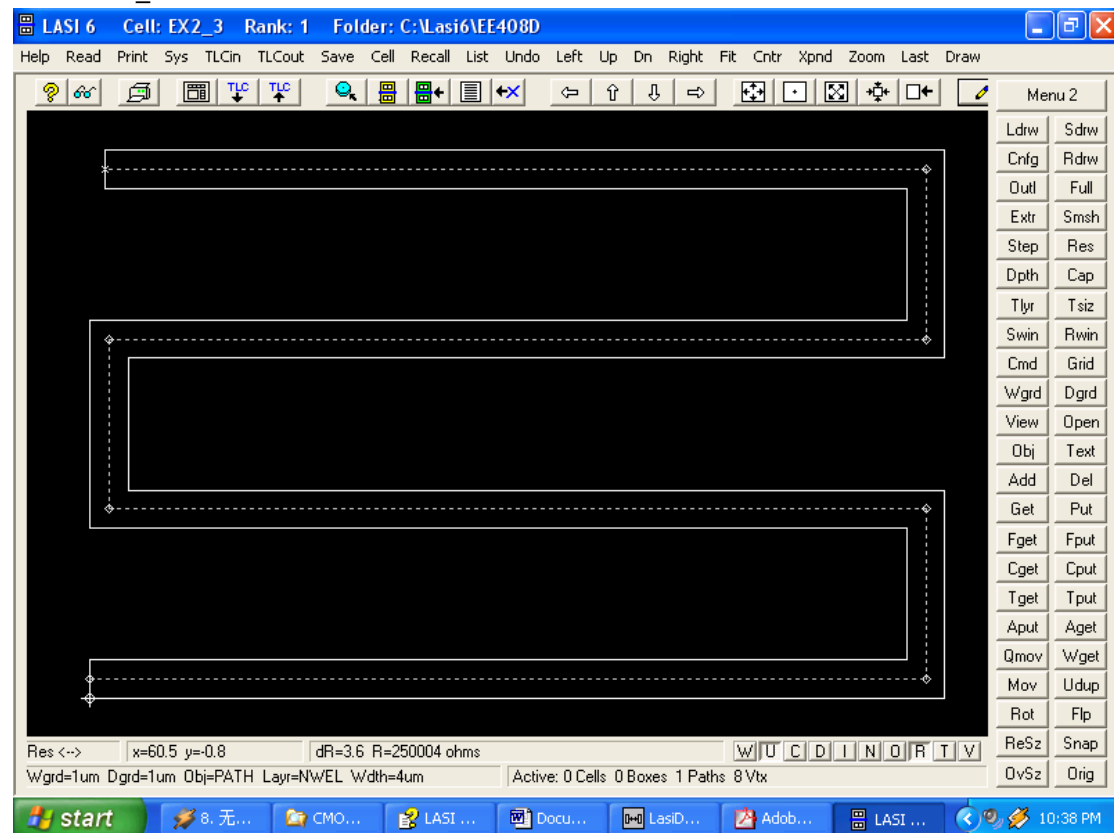


HW 2_SOLUTION

Problem 2_3



1. Draw the graph by “Path”; define the width of the path is 4um ($W_s=4\mu\text{m}$) ; the maximum length of a segment is 86um ($L_s=86\mu\text{m}$). Define width between horizontal line is $W_g=13.87\mu\text{m}$. Notice that the maximum length of the resistor is $86+4=90\mu\text{m}<100\mu\text{m}$.
2. Also, this design has passed the LASIDRC check. ($W_g=13.87\mu\text{m}>9\mu\text{m}$, $W_s=4\mu\text{m}>3\mu\text{m}$).
3. Define SheetResistance $R(\text{square})=2.5\text{k Ohm}$. As shown above, the total resistance of this resistor is $R=250004\text{Ohm}=250\text{k Ohm}$.

Problem 2.7.

According to Ex. 2.3,

$$C_j = C_{j0} / (1 - (V_d / 0.7))^{0.33} = 1.12 \text{ pF} / (1 - (-1/0.7))^{0.33} = 0.8357 \text{ pF}$$

$$f_{3\text{db}} = 1 / (2\pi RC) = 1 / (2 \times \pi \times 10\text{k} \times 0.8357 \text{ pF}) \approx 19 \text{ Mhz}$$

Problem 2.10

For $5\mu\text{m} \times 2000\mu\text{m}$ nwell, the capacitance C is simply the product of the bottom area of the resistor with the zero-bias depletion capacitance.

$$C = 100\text{aF} \times 5^2 \times 400 = 1\text{pF}, R = 1\text{M}\Omega$$

Therefore, the delay is given by

$$t_d = 0.35RC = 0.35 \times 1\text{pF} \times 1\text{M}\Omega = 0.35\mu\text{s}$$

Problem 2.14.

The diode storage time is given by

$$t_s = \tau_T \cdot \ln \left(\frac{i_F - i_R}{(-i_R)} \right),$$

$$i_F = V_F / R = (5-0.7)\text{V} / 1\text{K}\Omega = 4.3\text{mA}, i_R = V_R / R = (-5-0.7)\text{V} / 1\text{K}\Omega = -5.7\text{mA}$$

Therefore,

$$t_s = 5\text{ns} \times \ln(10/5.7) \approx 2.81\text{ns}$$

5. For a PN junction with uniform doping of $N_A = 10^{17}/\text{cm}^3$ and $N_D = 10^{17}/\text{cm}^3$, calculate the built-in potential, width of the depletion region, and the junction capacitance.

Ans:

Built-in Potential:

$$\phi_{bi} = V_T \ln \left(\frac{N_A N_D}{n_i^2} \right) = 0.026 \times \ln \left(\frac{10^{17} \times 10^{17}}{(1.45 \times 10^{10})^2} \right) = 0.83\text{V}$$

Width:

$$X_d = \sqrt{\frac{2\epsilon_s}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) \phi_{bi}} = \sqrt{\frac{2 \times 1.036 \times 10^{-12}}{1.6 \times 10^{-19}} \left(\frac{1}{10^{17}} + \frac{1}{10^{17}} \right) \times 0.83} = 0.147\mu\text{m}$$

Junction capacitance:

$$C_j = \frac{\epsilon_s}{X_d} = \frac{1.036 \times 10^{-12} \text{ F/cm}}{0.147\mu\text{m}} = 7.16 \times 10^{-8} \text{ F/cm}^2$$